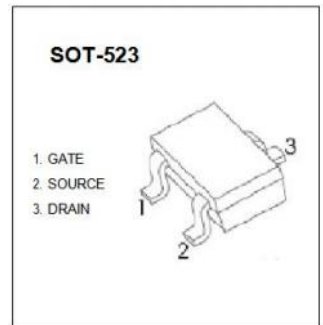
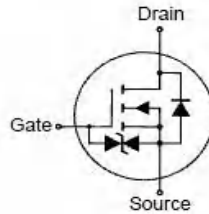




### 2N7002KT N-Channel Enhancement Mode Field Effect Transistor

#### Features

- Low on resistance  $R_{DS(ON)}$
- Low gate threshold voltage
- Low input capacitance
- ESD protected up to 2KV



**MARKING: 72K**

#### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	60	V
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V
Drain Current (Continuous)	$I_D$	300	mA
Drain Current (Pulse Width $\leq 10\text{ }\mu\text{s}$ )	$I_{DM}$	800	mA
Total Power Dissipation	$P_{tot}$	350	mW
Operating and Storage Temperature Range	$T_j, T_{stg}$	- 55 to + 150	$^\circ\text{C}$

#### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Drain Source Breakdown Voltage at $I_D = 10\text{ }\mu\text{A}$	$BV_{DSS}$	60	-	V
Zero Gate Voltage Drain Current at $V_{DS} = 60\text{ V}$	$I_{DSS}$	-	1	$\mu\text{A}$
Gate Source Leakage Current at $V_{GS} = \pm 20\text{ V}$	$I_{GSS}$	-	$\pm 10$	$\mu\text{A}$
Gate Threshold Voltage at $V_{DS} = 10\text{ V}, I_D = 250\text{ }\mu\text{A}$	$V_{GS(th)}$	1	2.5	V
Static Drain Source On-Resistance at $V_{GS} = 10\text{ V}, I_D = 500\text{ mA}$ at $V_{GS} = 4.5\text{ V}, I_D = 200\text{ mA}$	$R_{DS(ON)}$	- -	3 4	$\Omega$
Forward Transconductance at $V_{DS} = 10\text{ V}, I_D = 200\text{ mA}$	$g_{fs}$	80	-	mS
Input Capacitance at $V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	$C_{iss}$	-	50	pF
Output Capacitance at $V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	$C_{oss}$	-	25	pF
Reverse Transfer Capacitance at $V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	$C_{rss}$	-	5	pF

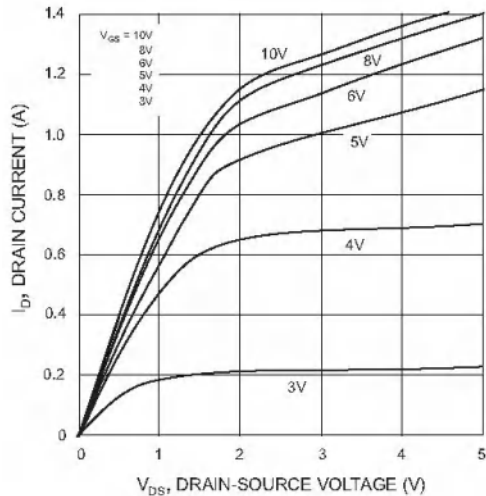


Fig. 1 Typical Output Characteristics

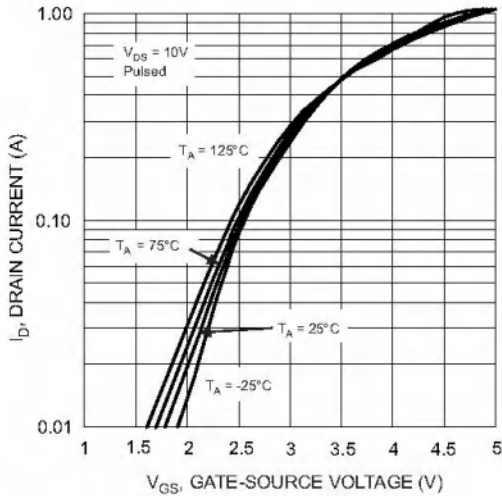


Fig. 2 Typical Transfer Characteristics

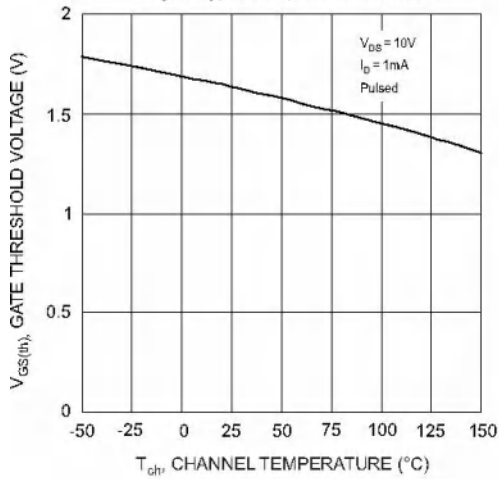


Fig. 3 Gate Threshold Voltage vs. Channel Temperature

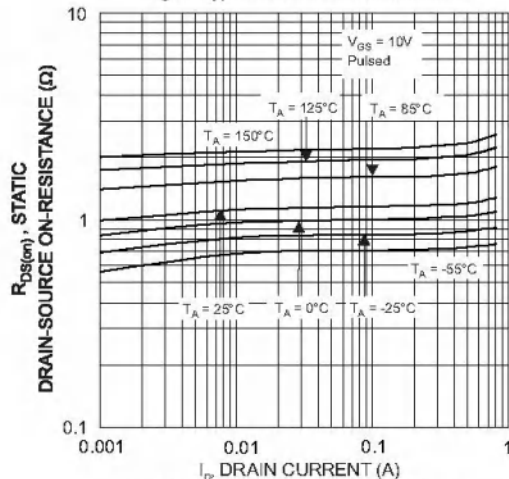


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

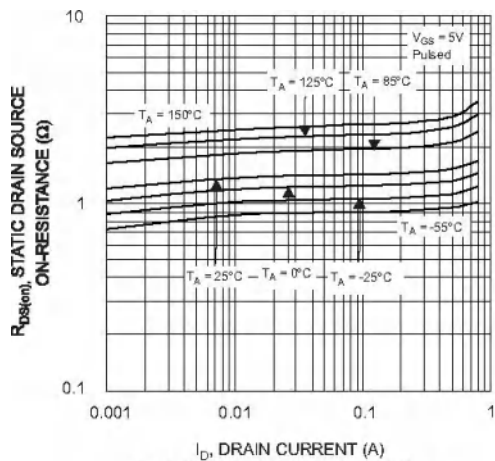


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current

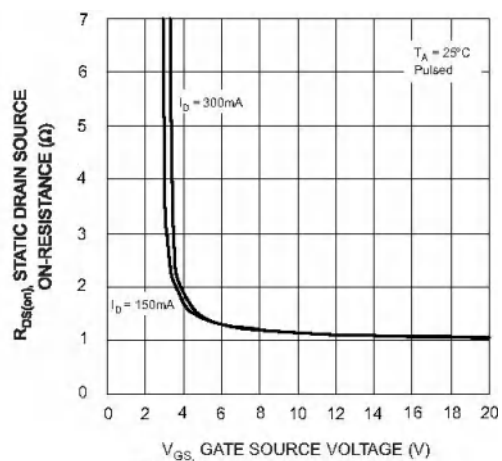
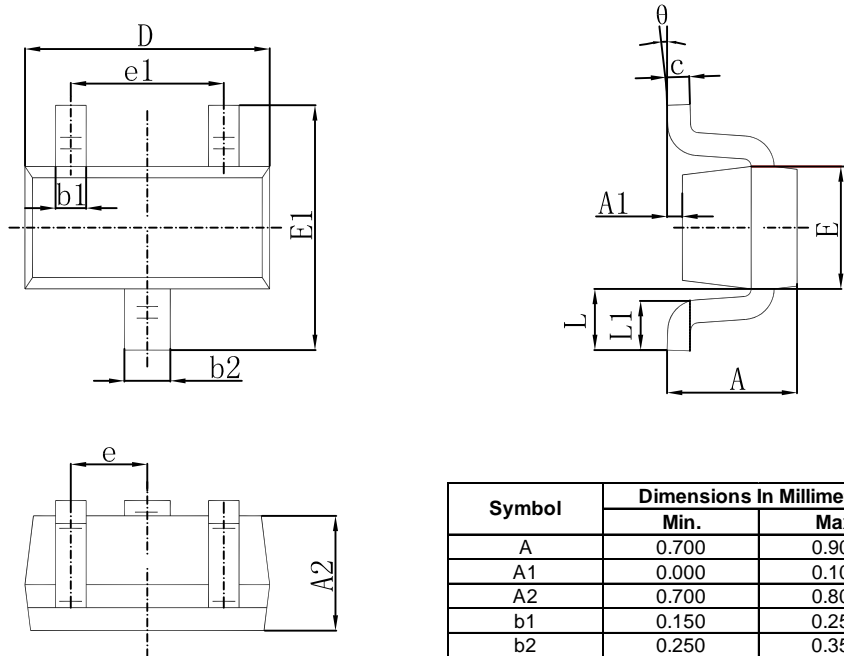


Fig. 6 Static Drain-Source On-Resistance vs. Gate-Source Voltage

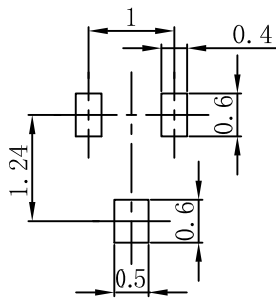


## SOT-523 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500 TYP.		0.020 TYP.	
e1	0.900	1.100	0.035	0.043
L	0.400 REF.		0.016 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

## SOT-523 Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance:  $\pm 0.05\text{mm}$ .
3. The pad layout is for reference purposes only.